Jin-Seong Park

List of Publications by Year
in descending order

265 papers	11,700 citations	36303 51 h-index	34986 98 g-index
267 all docs	267 docs citations	267 times ranked	8278 citing authors

#	Article	IF	Citations
1	Delamination of Graphene/ZnO interlayer driven by photocatalytic effect for flexible a-IGZO TFT applications. Applied Surface Science, 2022, 571, 151358.	6.1	3
2	Highly Efficient Bifacial Colorâ€Tunable Perovskite Solar Cells. Advanced Optical Materials, 2022, 10, 2101696.	7.3	7
3	Facile synthesis of an organic/inorganic hybrid 2D structure tincone film by molecular layer deposition. Dalton Transactions, 2022, 51, 1829-1837.	3.3	3
4	Impact of Annealing Temperature on Atomic Layer Deposited Inâ€“Gaâ€“Znâ€“O Thin-Film Transistors. ACS Applied Electronic Materials, 2022, 4, 1343-1350.	4.3	10
5	Atmospheric pressure spatial ALD of Al2O3 thin films for flexible PEALD IGZO TFT application. Ceramics International, 2022, 48, 18803-18810.	4.8	13
6	Plasma-enhanced atomic layer deposition of aluminum-indium oxide thin films and associated device applications. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, 032402.	2.1	3
7	Impact of N₂O Plasma Reactant on PEALD-SiO₂ Insulator for Remarkably Reliable ALD-Oxide Semiconductor TFTs. IEEE Transactions on Electron Devices, 2022, 69, 3199-3205.	3.0	6
8	Plasma-enhanced atomic-layer deposition of active layers of nanolaminated (InO_x)_n(GaZnO_y)_m for thin-film transistors. Journal of Materials Chemistry C, 2022, 10, 7831-7838.	5.5	4
9	Remarkable Stability Improvement with a Highâ€Performance PEALDâ€IZO/IGZO Topâ€Gate Thinâ€Film Transistor via Modulating Dualâ€Channel Effects. Advanced Materials Interfaces, 2022, 9, .	3.7	16
10	Structural, Optical, and Electrical Properties of InO_x Thin Films Deposited by Plasma-Enhanced Atomic Layer Deposition for Flexible Device Applications. ACS Applied Electronic Materials, 2022, 4, 3010-3017.	4.3	15
11	Plasma-enhanced atomic-layer-deposited indium oxide thin film using a DMION precursor within a wide process window. Ceramics International, 2022, 48, 27807-27814.	4.8	12
12	Pâ€3: High Temperature Annealing Behavior of IGZO Using Plasma Enhanced Atomic Layer Deposition. Digest of Technical Papers SID International Symposium, 2022, 53, 1047-1050.	0.3	0
13	5â€3: A Random Access Gate Driver Using aâ€IGZO TFTs for External Compensation of Highâ€Resolution, Highâ€Frameâ€Rate AMOLEDs. Digest of Technical Papers SID International Symposium, 2022, 53, 32-35.	0.3	0
14	Pâ€2: Nitrogen Behaviors in PEALDâ€Grown SiO ₂ Films Using N ₂ O Plasma Reactant and Its Application in ALDâ€IZO TFTs. Digest of Technical Papers SID International Symposium, 2022, 53, 1043-1046.	0.3	0
15	Enhanced performance and stability in InGaZnO NIR phototransistors with alumina-infilled quantum dot solid. Scientific Reports, 2022, 12, .	3.3	3
16	Plasma Enhanced atomic layer deposited amorphous gallium oxide thin films using novel trimethyl[N-(2-methoxyethyl)-2-methylpropan-2-amine]gallium. Ceramics International, 2021, 47, 1588-1593.	4.8	5
17	Tailoring nanostructured NbCoSn-based thermoelectric materials via crystallization of an amorphous precursor. Nano Energy, 2021, 80, 105518.	16.0	19
18	An organicâ€“inorganic hybrid semiconductor for flexible thin film transistors using molecular layer deposition. Journal of Materials Chemistry C, 2021, 9, 4322-4329.	5.5	12

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19	Effects of Tensile Strain on Dynamic and Static Inverters Using Amorphous Indium-Gallium-Zinc-Oxide TFTs. IEEE Electron Device Letters, 2021, 42, 359-362.	3.9	2
20	Highly efficient and stable flexible perovskite solar cells enabled by using plasma-polymerized-fluorocarbon antireflection layer. Nano Energy, 2021, 82, 105737.	16.0	46
21	Low Subthreshold Swing and High Performance of Ultrathin PEALD InGaZnO Thin-Film Transistors. IEEE Transactions on Electron Devices, 2021, 68, 1670-1675.	3.0	20
22	Reduction of Persistent Photoconduction with IGZO/ZnON-Tandem-Structure Visibleâ€“Near-Infrared Phototransistors. ACS Applied Materials & Interfaces, 2021, 13, 17827-17834.	8.0	7
23	Extremely high photoconductivity ultraviolet-light sensor using amorphous Inâ€“Gaâ€“Znâ€“O thin-film-transistor. Journal of the Korean Physical Society, 2021, 78, 1221-1226.	0.7	3
24	Plasma-enhanced atomic layer deposited indium oxide film using a novel dimethylbutylamino-trimethylindium precursor for thin film transistors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	2.1	9
25	Undoped tin dioxide transparent electrodes for efficient and cost-effective indoor organic photovoltaics (SnO2 electrode for indoor organic photovoltaics). NPG Asia Materials, 2021, 13, .	7.9	36
26	Area-Selective Atomic Layer Deposition of Ruthenium Using a Novel Ru Precursor and H₂O as a Reactant. Chemistry of Materials, 2021, 33, 4353-4361.	6.7	17
27	Significance of Pairing In/Ga Precursor Structures on PEALD InGaO_x Thin-Film Transistor. ACS Applied Materials & Interfaces, 2021, 13, 28493-28502.	8.0	18
28	Highly Dense and Stable p-Type Thin-Film Transistor Based on Atomic Layer Deposition SnO Fabricated by Two-Step Crystallization. ACS Applied Materials & Interfaces, 2021, 13, 30818-30825.	8.0	28
29	Facile and Stable n⁺ Doping Process Via Simultaneous Ultraviolet and Thermal Energy for Coplanar ALD-IGZO Thin-Film Transistors. ACS Applied Electronic Materials, 2021, 3, 3530-3537.	4.3	11
30	Atomic layer chemical vapor deposition of SiO2 thin films using a chlorine-free silicon precursor for 3D NAND applications. Ceramics International, 2021, 47, 19036-19042.	4.8	9
31	Atomic-Layer-Deposited SiO_x/SnO_x Nanolaminate Structure for Moisture and Hydrogen Gas Diffusion Barriers. ACS Applied Materials & Interfaces, 2021, 13, 39584-39594.	8.0	7
32	A study on the growth mechanism and gas diffusion barrier property of homogeneously mixed siliconâ€“tin oxide by atomic layer deposition. Ceramics International, 2021, 47, 34774-34782.	4.8	3
33	Plasma-enhanced atomic layer deposited HfO2 films using a novel heteroleptic cyclopentadienyl-based Hf precursor. Ceramics International, 2021, 47, 29030-29035.	4.8	7
34	Facile rearrangement of molecular layer deposited metalcone thin films by electron beam irradiation for area selective atomic layer deposition. Dalton Transactions, 2021, 50, 9958-9967.	3.3	6
35	Water vapor and hydrogen gas diffusion barrier characteristics of Al₂O₃â€“alucone multi-layer structures for flexible OLED display applications. Dalton Transactions, 2021, 50, 15841-15848.	3.3	6
36	The Significance on Structural Modulation of Buffer and Gate Insulator for ALD Based InGaZnO TFT Applications. IEEE Transactions on Electron Devices, 2021, 68, 6147-6153.	3.0	7

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37	High Field-Effect Mobility Two-Channel InGaZnO Thin-Film Transistors for Low-Voltage Operation. IEEE Transactions on Electron Devices, 2021, 68, 6166-6170.	3.0	1
38	Mechanical Durability of Flexible/Stretchable a-IGZO TFTs on PI Island for Wearable Electronic Application. ACS Applied Electronic Materials, 2021, 3, 5037-5047.	4.3	17
39	Dry-Etchable Molecular Layer-Deposited Inhibitor Using Annealed Indicone Film for Nanoscale Area-Selective Deposition. ACS Applied Materials & Interfaces, 2021, 13, 60144-60153.	8.0	6
40	Transparent Flexible High Mobility TFTs Based on ZnON Semiconductor With Dual Gate Structure. IEEE Electron Device Letters, 2020, 41, 401-404.	3.9	18
41	Organic/Inorganic Hybrid Buffer in InGaZnO Transistors under Repetitive Bending Stress for High Electrical and Mechanical Stability. ACS Applied Materials & Interfaces, 2020, 12, 3784-3791.	8.0	15
42	Impact of tandem IGZO/ZnON TFT with energy-band aligned structure. Applied Physics Letters, 2020, 117, 143505.	3.3	20
43	Metastable Rhombohedral Phase Transition of Semiconducting Indium Oxide Controlled by Thermal Atomic Layer Deposition. Chemistry of Materials, 2020, 32, 7397-7403.	6.7	33
44	Selective Nonenzymatic Amperometric Detection of Lactic Acid in Human Sweat Utilizing a Multi-Walled Carbon Nanotube (MWCNT)-Polypyrrole Core-Shell Nanowire. Biosensors, 2020, 10, 111.	4.7	23
45	Nanoscale surface engineering of a high-k ZrO₂/SiO₂ gate insulator for a high performance ITZO TFT via plasma-enhanced atomic layer deposition. Journal of Materials Chemistry C, 2020, 8, 13342-13348.	5.5	9
46	Thermal Annealing of Molecular Layer-Deposited Indicone Toward Area-Selective Atomic Layer Deposition. ACS Applied Materials & Interfaces, 2020, 12, 43212-43221.	8.0	11
47	Hydrogen Impacts of PEALD InGaZnO TFTs Using SiO_x Gate Insulators Deposited by PECVD and PEALD. IEEE Transactions on Electron Devices, 2020, 67, 4250-4255.	3.0	32
48	Plasma-Polymer-Fluorocarbon Thin Film Coated Nanostructured-Polyethylene Terephthalate Surface with Highly Durable Superhydrophobic and Antireflective Properties. Polymers, 2020, 12, 1026.	4.5	11
49	A bow-free freestanding GaN wafer. RSC Advances, 2020, 10, 21860-21866.	3.6	1
50	Study on efficiency improvement of multi-crystalline silicon solar cell by removing by-product and plasma induced damage generated during reactive ion etching. Current Applied Physics, 2020, 20, 519-524.	2.4	5
51	Investigating the interface characteristics of high-k ZrO2/SiO2 stacked gate insulator grown by plasma-enhanced atomic layer deposition for improving the performance of InSnZnO thin film transistors. AIP Advances, 2020, 10, .	1.3	4
52	Soft Recovery Process of Mechanically Degraded Flexible a-IGZO TFTs With Various Rolling Stresses and Defect Simulation Using TCAD Simulation. IEEE Transactions on Electron Devices, 2020, 67, 535-541.	3.0	17
53	Molecular layer deposition of indicone and organic-inorganic hybrid thin films as flexible transparent conductor. Applied Surface Science, 2020, 525, 146383.	6.1	16
54	Air-stable alucone thin films deposited by molecular layer deposition using a 4-mercaptophenol organic reactant. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, 022411.	2.1	9

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55	Recent review on improving mechanical durability for flexible oxide thin film transistors. Journal Physics D: Applied Physics, 2019, 52, 483002.	2.8	8
56	Electrical Stability Analysis of Dynamic Logic Using Amorphous Indiumâ€“Galliumâ€“Zinc-Oxide TFTs. IEEE Electron Device Letters, 2019, 40, 1128-1131.	3.9	8
57	Plasma enhanced atomic layer deposited silicon dioxide with divalent Si precursor [N,Nâ€²-tert-butyl-1,1-dimethylethylenediamine silylene]. Applied Surface Science, 2019, 493, 125-130.	6.1	2
58	Ultra-High-Speed Intense Pulsed-Light Irradiation Technique for High-Performance Zinc Oxynitride Thin-Film Transistors. ACS Applied Materials & Interfaces, 2019, 11, 4152-4158.	8.0	18
59	Amorphous IGZO TFT with High Mobility of â^¼70 cm²/(V s) via Vertical Dimension Control Using PEALD. ACS Applied Materials & Interfaces, 2019, 11, 40300-40309.	8.0	188
60	Cross-plane thermoelectric Seebeck coefficients in nanoscale Al2O3/ZnO superlattice films. Journal of Materials Chemistry C, 2019, 7, 1670-1680.	5.5	11
61	The impact of plasma-enhanced atomic layer deposited ZrSiOx insulators on low voltage operated In-Sn-Zn-O thin film transistors. Ceramics International, 2019, 45, 19166-19172.	4.8	19
62	Super-hydrophobic and antimicrobial properties of Ag-PPFC nanocomposite thin films fabricated using a ternary carbon nanotube-Ag-PTFE composite sputtering target. Surface and Coatings Technology, 2019, 370, 18-23.	4.8	35
63	Design of InZnSnO Semiconductor Alloys Synthesized by Supercycle Atomic Layer Deposition and Their Rollable Applications. ACS Applied Materials & Interfaces, 2019, 11, 12683-12692.	8.0	49
64	Efficiency characteristics of a silicon oxide passivation layer on p-type crystalline silicon solar cell at low illumination. Current Applied Physics, 2019, 19, 683-689.	2.4	13
65	Effects of porosity and particle size on the gas sensing properties of SnO2 films. Applied Surface Science, 2019, 481, 133-137.	6.1	57
66	Rapid gas-induced detachable rGO/MnO debonding layer for flexible electronic applications. Carbon, 2019, 146, 756-762.	10.3	3
67	Quantitative analysis of interface trap recovery caused by repetitive bending stress in flexible oxide thin-film transistors. Japanese Journal of Applied Physics, 2019, 58, 050906.	1.5	8
68	Improved performance and stability of In-Sn-Zn-O thin film transistor by introducing a meso-crystalline ZrO2 high-k gate insulator. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, .	2.1	20
69	Optimization of a SiOx/SiNxOyCz multilayer structure for a reliable gas diffusion barrier via low-temperature plasma-enhanced atomic layer deposition. Ceramics International, 2019, 45, 7407-7412.	4.8	5
70	Phase-controlled SnO2 and SnO growth by atomic layer deposition using Bis(N-ethoxy-2,2-dimethyl) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 5	4.8	42
71	Review of Organic/Inorganic Thin Film Encapsulation by Atomic Layer Deposition for a Flexible OLED Display. Jom, 2019, 71, 197-211.	1.9	68
72	Supreme performance of zinc oxynitride thin film transistors via systematic control of the photo-thermal activation process. Journal of Materials Chemistry C, 2018, 6, 5171-5175.	5.5	18

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73	The impact of carrier gas on the physical and electrical properties of indium oxide layers grown by mist-CVD. Ceramics International, 2018, 44, 6968-6972.	4.8	7
74	Rational design of protective In2O3 layer-coated carbon nanopaper membrane: Toward stable cathode for long-cycle Li-O2 batteries. Nano Energy, 2018, 46, 193-202.	16.0	58
75	Effects of helium concentration on microcrystalline silicon thin film solar cells deposited by atmospheric-pressure plasma deposition at 13.3â€¯kPa. Thin Solid Films, 2018, 650, 32-36.	1.8	5
76	Review of recent progresses on flexible oxide semiconductor thin film transistors based on atomic layer deposition processes. Journal of Semiconductors, 2018, 39, 011008.	3.7	48
77	Photothermally Activated Nanocrystalline Oxynitride with Superior Performance in Flexible Field-Effect Transistors. ACS Applied Materials & Interfaces, 2018, 10, 2709-2715.	8.0	13
78	Efficient Planar Perovskite Solar Cells Using Passivated Tin Oxide as an Electron Transport Layer. Advanced Science, 2018, 5, 1800130.	11.2	120
79	The effect of solvent water content on the dielectric properties of Al2O3 films grown by atmospheric pressure mist-CVD. Ceramics International, 2018, 44, 459-463.	4.8	14
80	Long-term air-stable Au doping of graphene by layer-by-layer assembly with graphene oxide for flexible transparent electrodes. Carbon, 2018, 126, 241-246.	10.3	20
81	A study on the thermoelectric properties of ALD-grown aluminum-doped tin oxide with respect to nanostructure modulations. Ceramics International, 2018, 44, 1978-1983.	4.8	14
82	Undoped ZnO electrodes for low-cost indoor organic photovoltaics. Journal of Materials Chemistry A, 2018, 6, 23464-23472.	10.3	38
83	Direct Probing of Cross-Plane Thermal Properties of Atomic Layer Deposition Al₂O₃/ZnO Superlattice Films with an Improved Figure of Merit and Their Cross-Plane Thermoelectric Generating Performance. ACS Applied Materials & Interfaces, 2018, 10, 44472-44482.	8.0	14
84	Review Article: Atomic layer deposition for oxide semiconductor thin film transistors: Advances in research and development. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	2.1	82
85	Selective SnO_x Atomic Layer Deposition Driven by Oxygen Reactants. ACS Applied Materials & Interfaces, 2018, 10, 33335-33342.	8.0	28
86	The pretreatment of granular activated carbon using sodium persulfate and hydrogen peroxide under basic conditions: Properties, metal impregnation, and As(V) adsorption. Materials Chemistry and Physics, 2018, 218, 317-325.	4.0	4
87	Facile fabrication of p-type Al2O3/carbon nanocomposite films using molecular layer deposition. Applied Surface Science, 2018, 458, 864-871.	6.1	21
88	Semiconductor behavior of Li doped ZnSnO thin film grown by mist-CVD and the associated device property. Journal of Alloys and Compounds, 2018, 762, 881-886.	5.5	10
89	Comparative Study on Hydrogen Behavior in InGaZnO Thin Film Transistors with a SiO2/SiNx/SiO2 Buffer on Polyimide and Glass Substrates. Electronic Materials Letters, 2018, 14, 749-754.	2.2	10
90	Chemistry of SiNx thin film deposited by plasma-enhanced atomic layer deposition using di-isopropylaminosilane (DIPAS) and N2 plasma. Ceramics International, 2018, 44, 20890-20895.	4.8	9

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91	Near-Infrared Photoresponsivity of ZnON Thin-Film Transistor with Energy Band-Tunable Semiconductor. ACS Applied Materials & Interfaces, 2018, 10, 30541-30547.	8.0	16
92	Effects of Repetitive Mechanical Stress on Flexible Oxide Thin-Film Transistors and Stress Reduction via Additional Organic Layer. IEEE Electron Device Letters, 2018, 39, 971-974.	3.9	24
93	A High-Reliability Carry-Free Gate Driver for Flexible Displays Using a-IGZO TFTs. IEEE Transactions on Electron Devices, 2018, 65, 3269-3276.	3.0	18
94	Electrochemical Corrosion and Hydrogen Diffusion Behaviors of Zn and Al Coated Hot-Press Forming Steel Sheets in Chloride Containing Environments. Korean Journal of Materials Research, 2018, 28, 286-294.	0.2	4
95	Compositional and electrical modulation of niobium oxide thin films deposited by plasma-enhanced atomic layer deposition. Ceramics International, 2017, 43, 6580-6584.	4.8	13
96	Anisotropic temperature-dependent thermal conductivity by an Al₂O₃ interlayer in Al₂O₃/ZnO superlattice films. Nanotechnology, 2017, 28, 105401.	2.6	12
97	Facile synthesis of AlO x dielectrics via mist-CVD based on aqueous solutions. Ceramics International, 2017, 43, 8932-8937.	4.8	9
98	Silicon oxide film deposited at room temperatures using high-working-pressure plasma-enhanced chemical vapor deposition: Effect of O2 flow rate. Ceramics International, 2017, 43, 10628-10631.	4.8	3
99	Atomic Layer Deposition of an Indium Gallium Oxide Thin Film for Thin-Film Transistor Applications. ACS Applied Materials & Interfaces, 2017, 9, 23934-23940.	8.0	97
100	High-Performance Zinc Tin Oxide Semiconductor Grown by Atmospheric-Pressure Mist-CVD and the Associated Thin-Film Transistor Properties. ACS Applied Materials & Interfaces, 2017, 9, 20656-20663.	8.0	23
101	Low temperature SiOx thin film deposited by plasma enhanced atomic layer deposition for thin film encapsulation applications. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	2.1	26
102	Effect of mechanical stress on the stability of flexible InGaZnO thin-film transistors. Journal of Information Display, 2017, 18, 87-91.	4.0	30
103	Control of phonon transport by the formation of the Al₂O₃ interlayer in Al₂O₃â€“ZnO superlattice thin films and their in-plane thermoelectric energy generator performance. Nanoscale, 2017, 9, 7027-7036.	5.6	40
104	Reduction of persistent photoconduction in Ge-Ga-In-O semiconductors by the incorporation of nitrogen. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, 021202.	1.2	4
105	Studies of thermoelectric transport properties of atomic layer deposited gallium-doped ZnO. Ceramics International, 2017, 43, 7784-7788.	4.8	27
106	Low temperature atomic layer deposition of SiO2 thin films using di-isopropylaminosilane and ozone. Ceramics International, 2017, 43, 2095-2099.	4.8	47
107	Three-dimensionally stacked Al2O3/graphene oxide for gas barrier applications. Carbon, 2017, 125, 464-471.	10.3	21
108	Review of recent advances in flexible oxide semiconductor thin-film transistors. Journal of Information Display, 2017, 18, 159-172.	4.0	97

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109	Dynamic Logic Circuits Using a-IGZO TFTs. IEEE Transactions on Electron Devices, 2017, 64, 4123-4130.	3.0	22
110	Effect of hydrogen on the device performance and stability characteristics of amorphous InGaZnO thin-film transistors with a SiO2/SiNx/SiO2 buffer. Applied Physics Letters, 2017, 111, .	3.3	34
111	Performance and Stability Enhancement of Inâ€“Snâ€“Znâ€“O TFTs Using SiO₂ Gate Dielectrics Grown by Low Temperature Atomic Layer Deposition. ACS Applied Materials & Interfaces, 2017, 9, 42928-42934.	8.0	50
112	The resonant interaction between anions or vacancies in ZnON semiconductors and their effects on thin film device properties. Scientific Reports, 2017, 7, 2111.	3.3	21
113	Enhanced charge collection with passivation of the tin oxide layer in planar perovskite solar cells. Journal of Materials Chemistry A, 2017, 5, 12729-12734.	10.3	103
114	All In-Plane Thermoelectric Properties of Atomic Layer Deposition-Grown Al₂O₃/ZnO Superlattice Film in the Temperature Range from 300 to 500 K. Science of Advanced Materials, 2017, 9, 1296-1301.	0.7	3
115	Anti-reflective conducting indium oxide layer on nanostructured substrate as a function of aspect ratio. Applied Physics Letters, 2016, 109, 121604.	3.3	1
116	The effect of ITO and Mo electrodes on the properties and stability of In-Ga-Zn-O thin film transistors. Journal of Electroceramics, 2016, 36, 129-134.	2.0	9
117	Boosting Responsivity of Organicâ€“Metal Oxynitride Hybrid Heterointerface Phototransistor. ACS Applied Materials & Interfaces, 2016, 8, 14665-14670.	8.0	25
118	Atomic layer deposition of indium oxide thin film from a liquid indium complex containing 1-dimethylamino-2-methyl-2-propoxy ligands. Applied Surface Science, 2016, 383, 1-8.	6.1	19
119	Low-Temperature Growth of Indium Oxide Thin Film by Plasma-Enhanced Atomic Layer Deposition Using Liquid Dimethyl(N-ethoxy-2,2-dimethylpropanamido)indium for High-Mobility Thin Film Transistor Application. ACS Applied Materials & Interfaces, 2016, 8, 26924-26931.	8.0	59
120	Photomodulation of InGaZnO thin film transistors with interfacial silver nanoparticles. Japanese Journal of Applied Physics, 2016, 55, 111101.	1.5	2
121	Enhancing the thermoelectric properties of super-lattice Al2O3/ZnO atomic film via interface confinement. Ceramics International, 2016, 42, 14411-14415.	4.8	32
122	Photoresponses of InSnGaO and InGaZnO thin-film transistors. RSC Advances, 2016, 6, 83529-83533.	3.6	7
123	Flexible and High-Performance Amorphous Indium Zinc Oxide Thin-Film Transistor Using Low-Temperature Atomic Layer Deposition. ACS Applied Materials & Interfaces, 2016, 8, 33821-33828.	8.0	124
124	Control of valley degeneracy in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Mo</mml:mi><mml:msub><mml:mi mathvariant="normal">S</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math>by layer thickness and electric field and its effect on thermoelectric properties. Physical Review B, 2016, 93, .	3.2	68
125	Performance modulation of transparent ALD indium oxide films on flexible substrates: transition between metal-like conductor and high performance semiconductor states. Journal of Materials Chemistry C, 2016, 4, 7571-7576.	5.5	43
126	A Study on the Electrical Properties of Atomic Layer Deposition Grown InO_x on Flexible Substrates with Respect to N₂O Plasma Treatment and the Associated Thin-Film Transistor Behavior under Repetitive Mechanical Stress. ACS Applied Materials & Interfaces, 2016, 8, 31136-31143.	8.0	62

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127	Enhancement of In-Sn-Ga-O TFT performance by the synergistic combination of UVÂ+ÂO3 radiation and low temperature annealing. Journal of Electroceramics, 2016, 37, 158-162.	2.0	17
128	A study on the electron transport properties of ZnON semiconductors with respect to the relative anion content. Scientific Reports, 2016, 6, 24787.	3.3	38
129	A Study on the Growth Behavior and Stability of Molecular Layer Deposited Alucone Films Using Diethylene Glycol and Trimethyl Aluminum Precursors, and the Enhancement of Diffusion Barrier Properties by Atomic Layer Deposited Al₂O₃ Capping. ACS Applied Materials & Interfaces, 2016, 8, 12263-12271.	8.0	36
130	Plasma-enhanced atomic layer deposition of tantalum nitride thin films using tertiary-amylimido-tris(dimethylamido)tantalum and hydrogen plasma. Journal of Electroceramics, 2016, 36, 165-169.	2.0	7
131	Growth of tantalum nitride film as a Cu diffusion barrier by plasma-enhanced atomic layer deposition from bis((2-(dimethylamino)ethyl)(methyl)amido)methyl(tert-butylimido)tantalum complex. Applied Surface Science, 2016, 362, 176-181.	6.1	16
132	A morphology, porosity and surface conductive layer optimized MnCo₂O₄ microsphere for compatible superior Li⁺ ion/air rechargeable battery electrode materials. Dalton Transactions, 2016, 45, 5064-5070.	3.3	17
133	Atomic layer deposited p-type copper oxide thin films and the associated thin film transistor properties. Ceramics International, 2016, 42, 5517-5522.	4.8	55
134	AOS TFTs for AMOLED TV. , 2016, , 997-1015.		1
135	Antireflective conducting nanostructures with an atomic layer deposited an AlZnO layer on a transparent substrate. Applied Surface Science, 2015, 357, 2385-2390.	6.1	5
136	Stability Improvement of In-Sn-Ga-O Thin-Film Transistors at Low Annealing Temperatures. IEEE Electron Device Letters, 2015, 36, 1160-1162.	3.9	43
137	Visible-light phototransistors based on InGaZnO and silver nanoparticles. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, .	1.2	19
138	Plasmon-enhanced photocurrent of Ge-doped InGaO thin film transistors using silver nanoparticles. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	2.1	14
139	Pâ€10: Comparative Studies of ZnON and ZnO Thin Film Transistors Fabricated by DC Reactive Sputtering Method. Digest of Technical Papers SID International Symposium, 2015, 46, 1155-1157.	0.3	0
140	Morphology Effect on Enhanced Li⁺-Ion Storage Performance for Ni^{2+/3+}and/or Co^{2+/3+}Doped LiMnPO₄Cathode Nanoparticles. Journal of Nanomaterials, 2015, 2015, 1-7.	2.7	4
141	Low temperature processed InGaZnO oxide thin film transistor using ultra-violet irradiation. Electronic Materials Letters, 2015, 11, 360-365.	2.2	12
142	Effect of Alumina Buffers on the Stability of Top-Gate Amorphous InGaZnO Thin-Film Transistors on Flexible Substrates. IEEE Electron Device Letters, 2015, 36, 917-919.	3.9	41
143	Highly Stable ZnON Thin-Film Transistors With High Field-Effect Mobility Exceeding 50 <inline-formula> <tex-math notation="LaTeX">cm^{2} </tex-math></inline-formula>/Vs. IEEE Electron Device Letters, 2015, 36, 38-40.	3.9	45
144	Temperature variable luminescence and color tuning of Eu²⁺/Mn²⁺-codoped strontium magnesium phosphates as promising red-emitting phosphors for light emitting diodes. Dalton Transactions, 2015, 44, 338-344.	3.3	9

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145	Ambient atmosphere-processable, printable Cu electrodes for flexible device applications: structural welding on a millisecond timescale of surface oxide-free Cu nanoparticles. Nanoscale, 2015, 7, 3997-4004.	5.6	42
146	Atomic layer deposition of highly conductive indium oxide using a liquid precursor and water oxidant. Ceramics International, 2015, 41, 10782-10787.	4.8	47
147	Facile Route to the Controlled Synthesis of Tetragonal and Orthorhombic SnO₂ Films by Mist Chemical Vapor Deposition. ACS Applied Materials & Interfaces, 2015, 7, 12074-12079.	8.0	43
148	Indium oxide thin film prepared by low temperature atomic layer deposition using liquid precursors and ozone oxidant. Journal of Alloys and Compounds, 2015, 649, 216-221.	5.5	51
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